

**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

ATTY DOCKET NO.  
FIS9-2001-0 295-US2

SERIAL NO. Divisional of  
10/047,964

Tze-Chiang Chen et al.

10-650890

FILING 8-28-03  
8/27/03

GROUP 5250 2825

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CL	6,043,152	03/28/2000	Chang et al.			
	6,080,529	06/27/2000	Ye et al.			
	6,099,701	08/08/2000	Liu et al.			
	6,107,188	08/22/2000	Liu et al.			
	6,127,238	10/03/2000	Liao et al.			
	6,153,523	11/28/2000	Van Ngo et al.			
	6,162,583	12/19/2000	Yang et al.			
	6,211,061 B1	04/03/2001	Chen et al.			
	6,218,732 B1	04/17/2001	Russell et al.			
	6,225,210 B1	05/01/2001	Ngo et al.			
CL	6,235,633 B1	05/22/2001	Jang			

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
CL	✓	WO 00/19523	06/06/2000	CA,CN,JP, European Patent				
	✓	JP2001015480A	01/19/2001	Japan				
	✓	JP2001053076A	02/23/2001	Japan				
	✓	JP1111843A	04/28/1989	Japan				
CL		WO 99/33102	07/01/1999	JP,KR, European Patent				

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

CL	✓	Soo Geun Lee et al., "Low Dielectric Constant 3MS a-SiC:H as Cu Diffusion Barrier Layer in Cu Dual Damascene Process," Japanese Journal of Applied Physics, Part 1, Vol. 40, No. 4B, pp. 2663-2668, April 2001.
CL	✓	R.D. Goldblatt et al., "A High Performance 0.13 um Copper BEOL Technology with Low-k Dielectric," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 261-263, June 5-7, 2000.

EXAMINER

calombur

DATE CONSIDERED

7.26.04

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.

FIS9-2001-0295- US2

SERIAL NO.

Divisional of  
10/047,964

10-650890

Tze-Chiang Chen et al.

FILING

8-28-03  
8-27-03

GROUP

2325

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
CL	6,261,951 B1	07/17/2001	Buchwalter et al.			
	US 2001/0000155 A1	04/05/2001	Huang et al.			
	US 2001/0002333 A1	05/31/2001	Huang et al.			
	US 2001/0002731 A1	06/07/2001	Ueda			
	US 2001/0003064 A1	06/07/2001	Ohto			
	6,265,779	07/24/01	Grill, et al.			
CL	6,441,491	08/27/02	Grill, et al.			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

CL	✓	J. Yota et al., "Comparison Between HDP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications," Proceedings of the IEEE 2000 International Interconnect Technology Conference, pp. 76-78, June 5-7, 2000.

EXAMINER

calomela

DATE CONSIDERED

7.26.04.

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.